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SBOS501A - JANUARY 2010-REVISED NOVEMBER 2010

PRECISION, LOW POWER INSTRUMENTATION AMPLIFIERS

Check for Samples: INA129-HT

FEATURES

Low Offset Voltage

Low Input Bias Current: 50 nA Typ

High CMR: 95 dB Typ
Inputs Protected to ±40 V

Wide Supply Range: ±2.25 V to ±18 V

Low Quiescent Current: 2 mA Typ

APPLICATIONS

Bridge Amplifier

Thermocouple Amplifier

RTD Sensor Amplifier

Medical Instrumentation

Data Acquisition

SUPPORTS EXTREME TEMPERATURE APPLICATIONS

Controlled Baseline

One Assembly/Test Site

One Fabrication Site

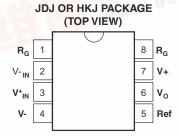
• Available in Extreme (-55°C/210°C)
Temperature Range(1)

Extended Product Life Cycle

• Extended Product-Change Notification

Product Traceability

 Texas Instruments' high temperature products utilize highly optimized silicon (die) solutions with design and process enhancements to maximize performance over extended temperatures.



(1) Custom temperature ranges available

DESCRIPTION

The INA129 is a low power, general purpose instrumentation amplifier offering excellent accuracy. The versatile three operational amplifier design and small size make it ideal for a wide range of applications. Current-feedback input circuitry provides wide bandwidth even at high gain.

A single external resistor sets any gain from 1 to 10,000. The INA129 gain equation is compatible with the AD620.

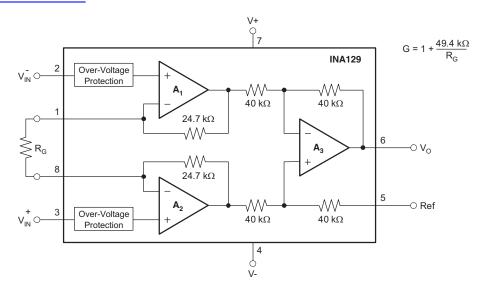
The INA129 is laser trimmed for very low offset voltage (50 μ V) and high common-mode rejection (93 dB at G \geq 100). It operates with power supplies as low as ± 2.25 V, and quiescent current of 2 mA - typically. Internal input protection can withstand up to ± 40 V without damage.

The INA129 is available in 8-pin ceramic DIP and 8-pin ceramic surface-mount packages, specified for the -55°C to 210°C temperature range.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





ORDERING INFORMATION

T _A	PACKAGE	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	HKJ	INA129SHKJ	INA129SHKJ
-55°C to 210°C	KGD	INA129SKGD1	NA
	JDJ	INA129SJD	INA129SJD

BARE DIE INFORMATION

DIE THICKNESS	DIE THICKNESS BACKSIDE FINISH		BOND PAD METALLIZATION COMPOSITION	
15 mm	Silicon with backgrind	GND	Al-Si-Cu (0.5%)	

Origin

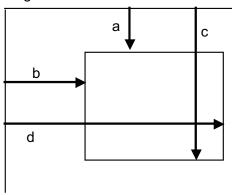
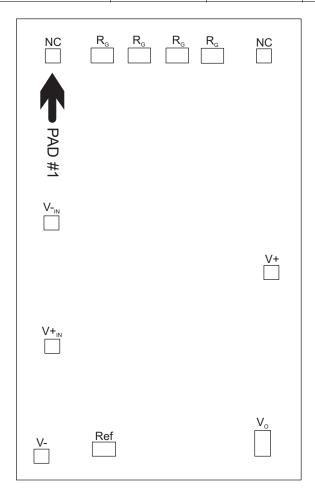




Table 1. Bond Pad Coordinates in Microns

DISCRIPTION	PAD NUMBER	а	b	С	d
NC	1	-57.4	-31.1	-53.3	-27
V-IN	2	-9.85	-31.4	-5.75	-27.3
V+ _{IN}	3	25.05	-31.4	29.15	-27.3
V-	4	56.2	-34.3	60.3	-30.2
Ref	5	53.75	-17.6	57.85	-11
Vo	6	50.35	27.8	56.95	31.9
V+	7	7.75	30.2	11.85	34.3
NC	8	-57.4	28.4	-53.3	32.5
R _G	9	-57.4	13.4	-53.3	20
R _G	10	-57.5	2.7	-53.4	9.3
R_{G}	11	-57.5	-7.9	-53.4	-1.3
R_{G}	12	-57.4	-18.6	-53.3	-12





ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

		VALUE	UNIT
Vs	Supply voltage	±18	V
	Analog input voltage range	±40	V
	Output short-circuit (to ground)	Continuous	•
T _A	Operating temperature	-55 to 210	°C
T _{STG}	Storage temperature range	-5 to 210	°C
	Lead temperature (soldering, 10s)	300	°C

⁽¹⁾ Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

242445552	TEST	T _A =	-55°C to 125°	°C	$T_A = 210^{\circ}C^{(1)}$			
PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
INPUT	1							
OFFSET VOLTAGE, RTI								
Initial	T _A = 25°C		±25 ±100/G	±125 ±1000/G				μV
vs temperature	$T_A = T_{MIN}$ to T_{MAX}		±0.2 ±5/G	±1 ±20/G		±1 ±850/G		μV/°C
vs power supply	V _S = ±2.25 V to ±18 V		±0.2 ±20/G	±2 ±200/G		±20 ±1000/G		μV/V
Long-term stability			±1 ±3/G			±1 ±3/G		μV/mo
Impedance, differential			10 ¹⁰ 2			10 ¹⁰ 2		Ω pF
Common mode			10 ¹¹ 9			10 ¹¹ 9		Ω pF
Common mode voltage range ⁽²⁾	V _O = 0 V	(V+) - 2	(V+) - 1.4		(V+) - 2	(V+) - 1.4		V
		(V-) + 2	(V−) + 1.7		(V-) + 2	(V−) + 1.7		V
Safe input voltage				±40			±40	V
	$V_{CM} = \pm 13 \text{ V},$ $\Delta R_S = 1 \text{ k}\Omega$							
	G = 1	58	86			53		
Common-mode rejection	G = 10	78	106			69		dB
	G = 100	99	125			89		aв
	G = 1000	113	130			95		
CURRENT								
Bias current			±2	±10		±50		nA
vs temperature			±30			±600		pA/°C
Offset Current			±1	±10		±50		nA
vs temperature			±30			±600		pA/°C

⁽¹⁾ Minimum and maximum parameters are characterized for operation at T_A = 210°C, but may not be production tested at that temperature. Production test limits with statistical guardbands are used to ensure high temperature performance.

⁽²⁾ Input common-mode range varies with output voltage — see typical curves.



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ELECTRICAL CHARACTERISTICS (continued)

over operating free-air temperature range (unless otherwise noted)

DAR	METER	TEST	T _A = -55°C to 125°C		Т	_A = 210°C ⁽¹⁾		UNIT		
PARA	AMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNII	
NOISE										
Noise voltag	e, RTI	G = 1000, $R_S = 0 \Omega$								
f = 10 Hz				10			25		nV/√Hz	
f = 100 H	Z			8			20		nV/√Hz	
f = 1 kHz				8			20		nV/√Hz	
f _B = 0.1 H	z to 10 Hz			0.2			2		μV_{PP}	
Noise currer										
f = 10 Hz				0.9					pA/√Hz	
f = 1 kHz				0.3					pA/√Hz	
f _B = 0.1 H	z to 10 Hz			30					pA _{PP}	
GAIN			I.							
Gain equation	on			1 + (49.4 kΩ/R _G)			1 + (49.4 kΩ/R _G)		V/V	
Range of ga	in		1		10000	1		10000	V/V	
		G = 1		±0.01	±0.1		±1.1			
0 :		G = 10		±0.02	±0.5		±2.6		٠,	
Gain error		G = 100		±0.05	±0.7		±13.5		%	
		G = 1000		±0.5	±2		±65.5			
Gain vs tem	perature ⁽³⁾	G = 1		±1	±10		±100		ppm/°C	
49.4-kΩ resistance ⁽³⁾⁽⁴⁾				±25	±100		±100		ppm/°C	
		V _O = ±13.6 V, G = 1		±0.0001	±0.001		±0.1			
Nonlinearity		G = 10		±0.0003	±0.002		±0.2		% of	
,		G = 100		±0.0005	±0.002		±0.7		FSR	
		G = 1000		±0.001	See (5)		±2.4	See (5)		
OUTPUT			1							
	Positive	$R_L = 10k\Omega$	(V+) - 1.4	(V+) - 0.9		(V+) - 1.4	(V+) - 0.9			
Voltage	Negative	$R_L = 10k\Omega$	(V−) + 1.4	(V-) + 0.8		(V−) + 1.4	(V-) + 0.8		V	
Load capaci	tance stability	_		1000		, ,	1000		pF	
Short-curcui	t current			+6/-15			+12/-5		mA	
FREQUENC	Y RESPONSE	1	II.							
		G = 1		1300			850			
		G = 10	700 400							
Bandwidth,	-3 dB	G = 100		200			50		kHz	
		G = 1000		20			7.5			
Slew rate		V _O = ±10 V, G = 10		4			4		V/µs	
		G = 1		7			10			
		G = 10		7			10			
Settling time	, 0.01%	G = 100		9			30		μs	
		G = 1000		80			150		+	
Overload red	covery	50% overdrive		4			4		μs	
POWER SU		<u>'</u>	I						'	

⁽³⁾ Specified by wafer test.

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⁽⁴⁾ Temperature coefficient of the 49.4-k Ω term in the gain equation.

⁽⁵⁾ Nonlinearity measurements in G = 1000 are dominated by noise. Typical nonlinearity is $\pm 0.001\%$.



ELECTRICAL CHARACTERISTICS (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST	$T_A = -55^{\circ}C \text{ to } 125^{\circ}C$			$T_A = 210^{\circ}C^{(1)}$			
	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
Voltage range		±2.25	±15	±18	±2.25	±15	±18	V
Current, total	V _{IN} = 0 V		±0.7	±0.75		±2		mA
TEMPERATURE RANGE								
Specification		-55		125			210	°C
Operating		-55		125			210	°C

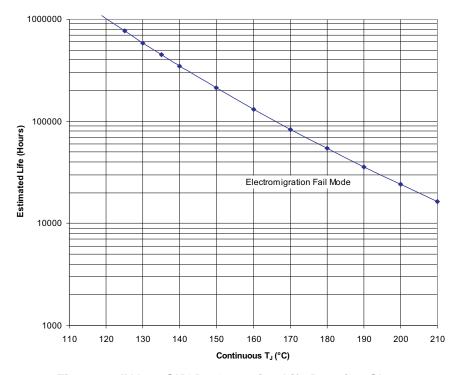


Figure 1. INA129SKGD1 Operating Life Derating Chart

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INSTRUMENTS

TYPICAL CHARACTERISTICS

At $T_A = 25$ °C, $V_S = \pm 15$ V, unless otherwise noted.

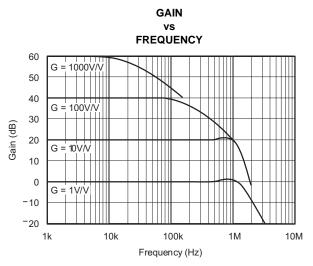


Figure 2.

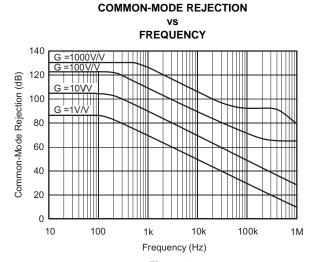


Figure 3.

POSITIVE POWER SUPPLY REJECTION

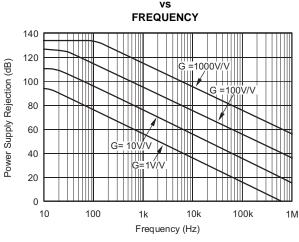


Figure 4.

NEGATIVE POWER SUPPLY REJECTION vs

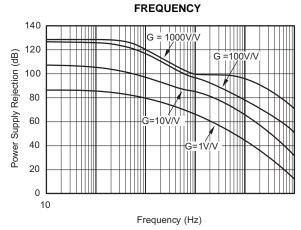


Figure 5.

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TYPICAL CHARACTERISTICS (continued)

At $T_A = 25$ °C, $V_S = \pm 15$ V, unless otherwise noted.

OUTPUT VOLTAGE $(V_S = \pm 15 \ V)$ 15 G ≥ 10 G ≥ 10 10 Common-Mode Voltage (V) G=1 G = 5) +15V 0 o V_o Ref 5 10 15 -15 -10 -5 0 10 15 Output Voltage (V)

INPUT COMMON-MODE RANGE

Figure 6.

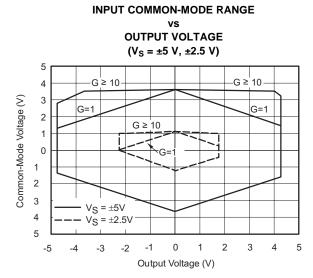


Figure 7.

INPUT-REFERRED NOISE



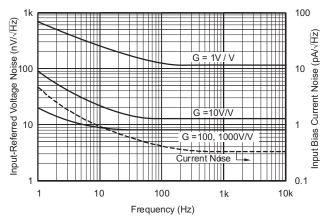


Figure 8.

SETTLING TIME

vs GAIN

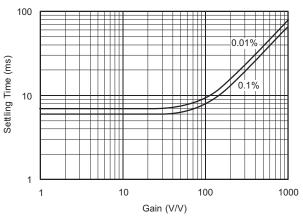


Figure 9.



TYPICAL CHARACTERISTICS (continued)

At $T_A = 25$ °C, $V_S = \pm 15$ V, unless otherwise noted.

QUIESCENT CURRENT AND SLEW RATE

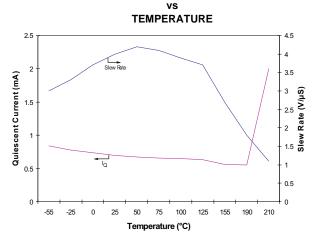


Figure 10.

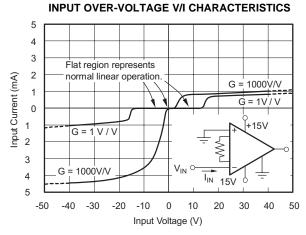


Figure 11.

INPUT OFFSET VOLTAGE WARM-UP

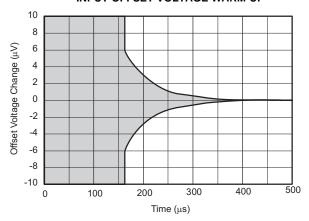


Figure 12.

INPUT BIAS CURRENT vs

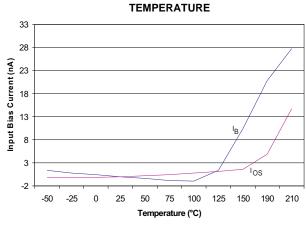
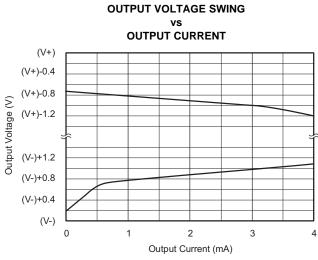


Figure 13.



TYPICAL CHARACTERISTICS (continued)

At $T_A = 25$ °C, $V_S = \pm 15$ V, unless otherwise noted.





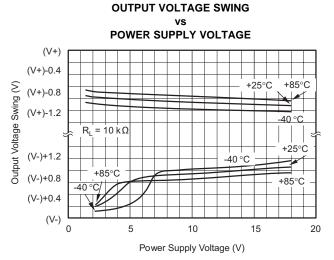


Figure 15.

SHORT-CIRCUIT OUTPUT CURRENT

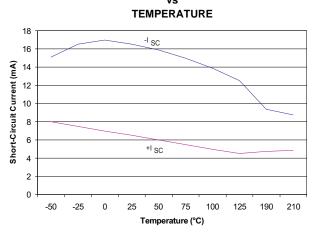
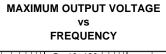


Figure 16.



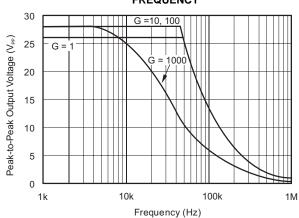


Figure 17.

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NSTRUMENTS

TYPICAL CHARACTERISTICS (continued)

At $T_A = 25$ °C, $V_S = \pm 15$ V, unless otherwise noted.

TOTAL HARMONIC DISTORTION + NOISE

FREQUENCY

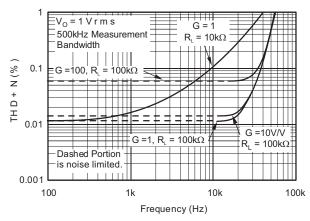


Figure 18.

SMALL SIGNAL (G = 100, 1000)

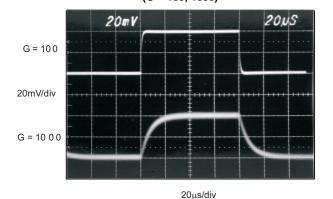


Figure 20.

LARGE SIGNAL (G = 100, 1000)

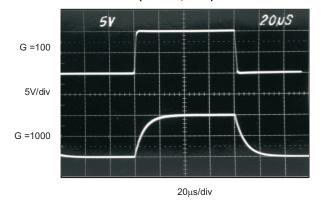


Figure 22.

SMALL SIGNAL (G = 1, 10)

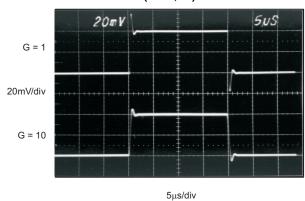


Figure 19.

LARGE SIGNAL (G = 1, 10)

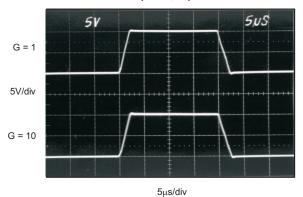
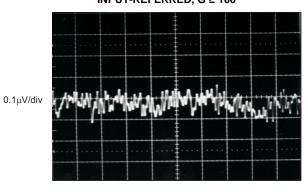


Figure 21.

VOLTAGE NOISE 0.1 Hz TO 10 Hz INPUT-REFERRED, G ≥ 100



1s/div

Figure 23.



APPLICATION INFORMATION

Figure 24 shows the basic connections required for operation of the INA129. Applications with noisy or high impedance power supplies may require decoupling capacitors close to the device pins as shown.

The output is referred to the output reference (Ref) terminal which is normally grounded. This must be a low-impedance connection to assure good common-mode rejection. A resistance of 8 Ω in series with the Ref pin will cause a typical device to degrade.

Setting the Gain

Gain is set by connecting a single external resistor, R_G, between pins 1 and 8.

$$G = 1 + \frac{49.4 \text{ k}\Omega}{R_G} \tag{1}$$

Commonly used gains and resistor values are shown in Figure 24.

The 49.9-k Ω term in Equation 1 comes from the sum of the two internal feedback resistors of A1 and A2. These on-chip metal film resistors are laser trimmed to accurate absolute values. The accuracy and temperature coefficient of these internal resistors are included in the gain accuracy and drift specifications of the INA129.

The stability and temperature drift of the external gain setting resistor, R_G , also affects gain. R_G 's contribution to gain accuracy and drift can be directly inferred from Equation 1. Low resistor values required for high gain can make wiring resistance important. Sockets add to the wiring resistance which will contribute additional gain error (possibly an unstable gain error) in gains of approximately 100 or greater.

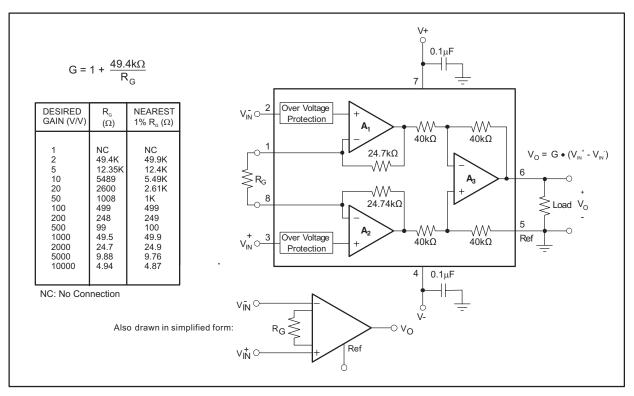


Figure 24. Basic Connections

Dynamic Performance

Figure 2 shows that, despite its low quiescent current, the INA129 achieves wide bandwidth, even at high gain. This is due to the current-feedback topology of the input stage circuitry. Settling time also remains excellent at high gain.

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Noise Performance

The INA129 provides very low noise in most applications. Low frequency noise is approximately 2 μ VPP measured from 0.1 Hz to 10 Hz (G \geq 100). This provides dramatically improved noise when compared to state-of-the-art chopper-stabilized amplifiers.

Offset Trimming

The INA129 is laser trimmed for low offset voltage and offset voltage drift. Most applications require no external offset adjustment. Figure 25 shows an optional circuit for trimming the output offset voltage. The voltage applied to Ref terminal is summed with the output. The operational amplifier buffer provides low impedance at the Ref terminal to preserve good common-mode rejection.

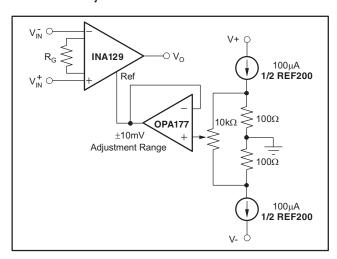


Figure 25. Optional Trimming of Output Offset Voltage

Input Bias Current Return Path

The input impedance of the INA129 is extremely high (approximately $10^{10} \Omega$). However, a path must be provided for the input bias current of both inputs. This input bias current is approximately ± 50 nA. High input impedance means that this input bias current changes very little with varying input voltage.

Input circuitry must provide a path for this input bias current for proper operation. Figure 26 shows various provisions for an input bias current path. Without a bias current path, the inputs will float to a potential which exceeds the common-mode range, and the input amplifiers will saturate.

If the differential source resistance is low, the bias current return path can be connected to one input (see the thermocouple example in Figure 26). With higher source impedance, using two equal resistors provides a balanced input with possible advantages of lower input offset voltage due to bias current and better high-frequency common-mode rejection.

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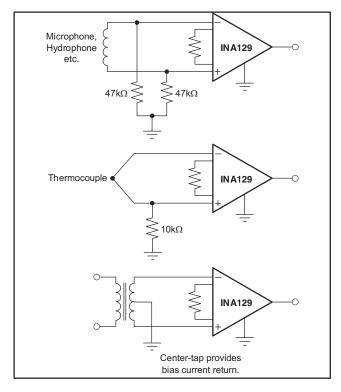


Figure 26. Providing an Input Common-Mode Current Path

Input Common-Mode Range

The linear input voltage range of the input circuitry of the INA129 is from approximately 1.4 V below the positive supply voltage to 1.7 V above the negative supply. As a differential input voltage causes the output voltage increase, however, the linear input range will be limited by the output voltage swing of amplifiers A1 and A2. So the linear common-mode input range is related to the output voltage of the complete amplifier. This behavior also depends on supply voltage (see Figure 6 and Figure 7).

Input-overload can produce an output voltage that appears normal. For example, if an input overload condition drives both input amplifiers to their positive output swing limit, the difference voltage measured by the output amplifier will be near zero. The output of A3 will be near 0 V even though both inputs are overloaded.

Low Voltage Operation

The INA129 can be operated on power supplies as low as ± 2.25 V. Performance remains excellent with power supplies ranging from ± 2.25 V to ± 18 V. Most parameters vary only slightly throughout this supply voltage range.

Operation at very low supply voltage requires careful attention to assure that the input voltages remain within their linear range. Voltage swing requirements of internal nodes limit the input common-mode range with low power supply voltage. Figure 6 and Figure 7 show the range of linear operation for ±15 V, ±5 V, and ±2.5 V supplies.



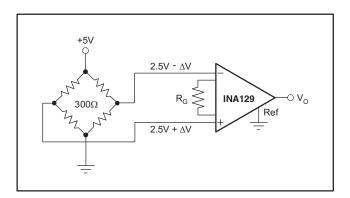


Figure 27. Bridge Amplifier

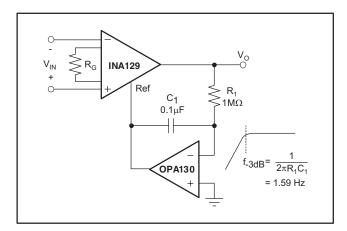


Figure 28. AC-Coupled Instrumentation Amplifier



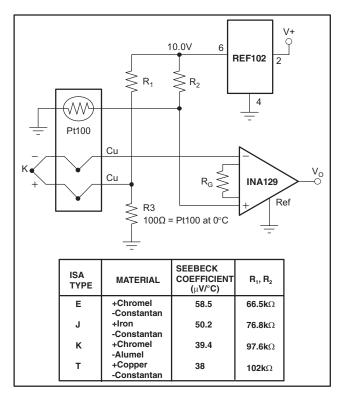


Figure 29. Thermocouple Amplifier With RTD Cold-Junction Compensation

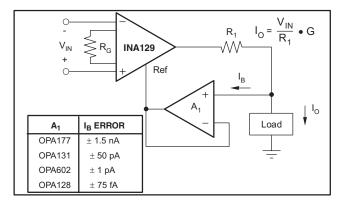


Figure 30. Differential Voltage to Current Converter

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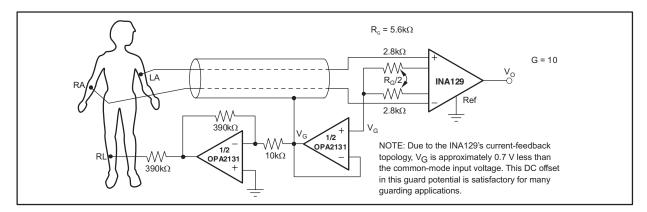


Figure 31. ECG Amplifier With Right-Leg Drive



PACKA(

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Pe
INA129SHKJ	ACTIVE	CFP	HKJ	8	25	TBD	Call TI	N / A for Pkg
INA129SJD	ACTIVE	CDIP SB	JDJ	8	45	TBD	POST-PLATE	N / A for Pkg
INA129SKGD1	ACTIVE	XCEPT	KGD	0	180	TBD	Call TI	N / A for Pkg

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www. information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retard in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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OTHER QUALIFIED VERSIONS OF INA129-HT:

Catalog: INA129



PACKA

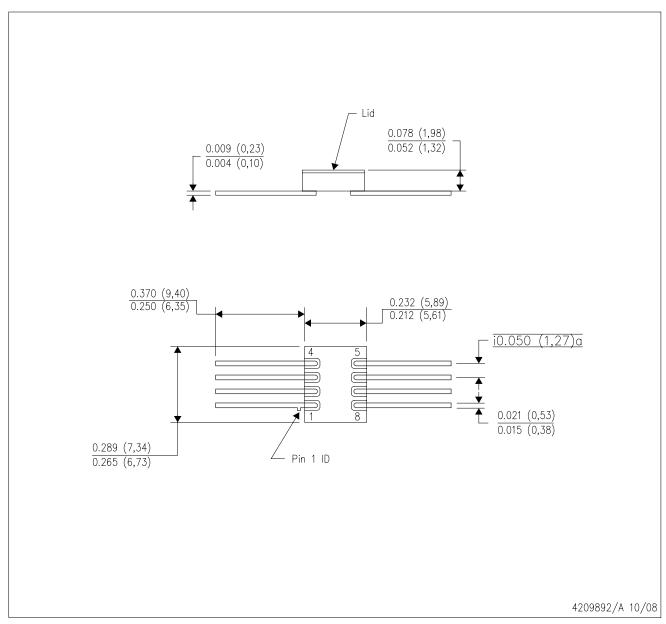
● Enhanced Product: INA129-EP

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Enhanced Product Supports Defense, Aerospace and Medical Applications

HKJ (R-CDFP-F8)

CERAMIC DUAL FLATPACK



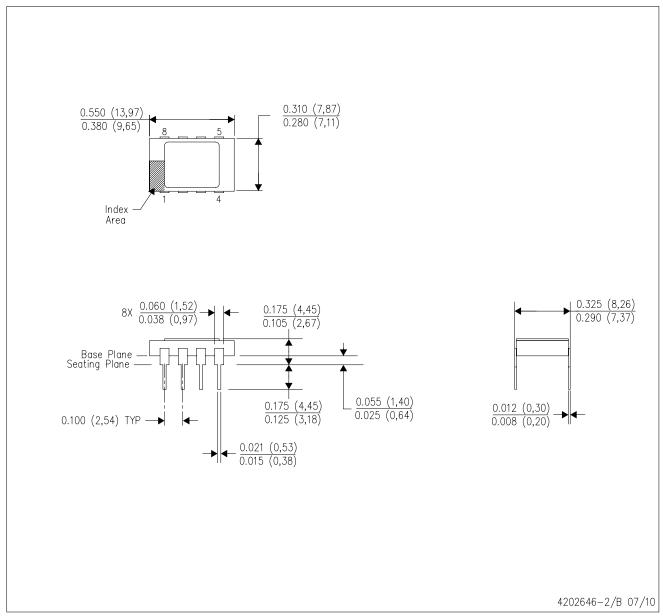
NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. The terminals will be gold plated.



JDJ (R-CDIP-T8)

CERAMIC DUAL IN-LINE PACKAGE



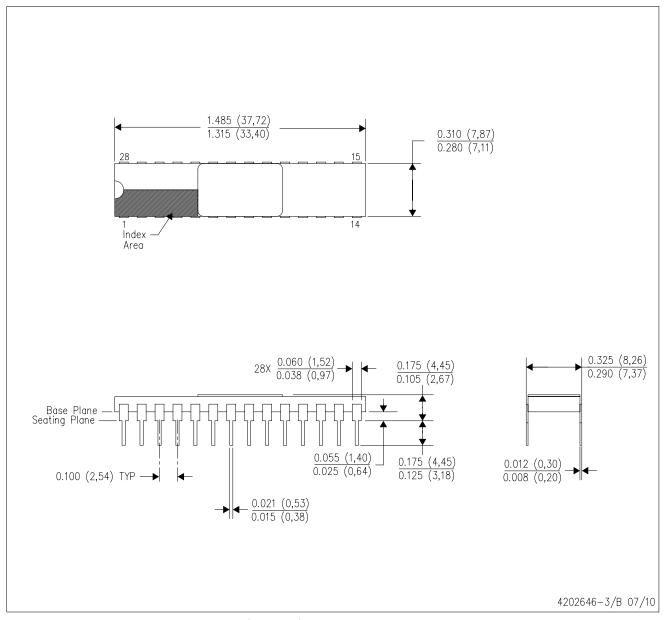
NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Ceramic quad flatpack with flat leads brazed to non-conductive tie bar carrier.
- D. This package is hermetically sealed with a metal lid.
- E. The leads are gold plated and can be solderdipped.
- F. Leads not shown for clarity purposes.
- G. Lid and heat sink are connected to GND leads.



JDJ (R-CDIP-T28)

CERAMIC DUAL IN-LINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Ceramic quad flatpack with flat leads brazed to non-conductive tie bar carrier.
- D. This package is hermetically sealed with a metal lid.
- E. The leads are gold plated and can be solderdipped.
- F. Leads not shown for clarity purposes.
- G. Lid and heat sink are connected to GND leads.



查询"INA129-HT"供应商

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